HM62W1664H Series

65536-word × 16-bit High Speed CMOS Static RAM

HITACHI

Description

The HM62W1664H is an asynchronous 3.3 V operation high speed static RAM organized as 64-kword × 16-bit. It realizes high speed access time (30/35/45 ns) with employing 0.8 µm CMOS process and high speed circuit designing technology. It is most appropriate for the application which requires high speed, high density memory and wide bit width configuration, such as cache and buffer memory in system. The HM62W1664H is packaged in 400-mil 44-pin SOJ for high density surface mounting.

Features

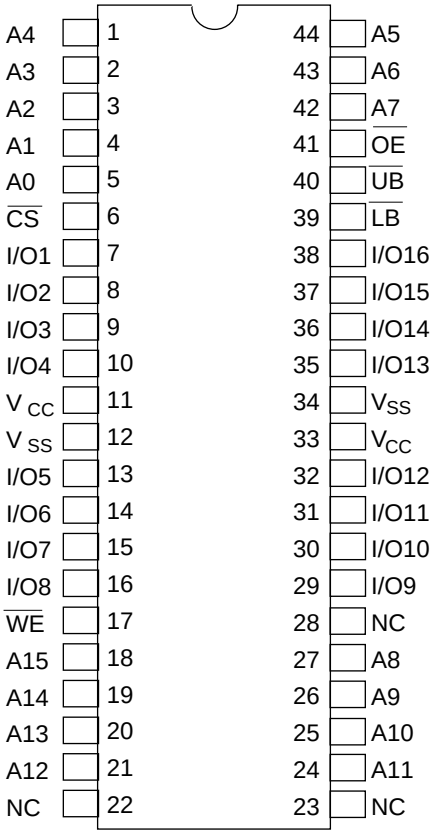
- Single 3.3 V supply: 3.3 V ± 0.3 V
- Access time 30/35/45 ns (max)
- Completely static memory
  - — No clock or timing strobe required
- Equal access and cycle times
- Directly CMOS compatible
  - — All inputs and outputs
- 400-mil 44-pin SOJ
- Center V_{CC} and V_{SS} type pinout

Ordering Information

Type No.	Access Time	Package
HM62W1664HJP-30	30 ns	400-mil 44-pin plastic SOJ (CP-44D)
HM62W1664HJP-35	35 ns	
HM62W1664HJP-45	45 ns	
HM62W1664HLJP-30	30 ns	
HM62W1664HLJP-35	35 ns	
HM62W1664HLJP-45	45 ns	

Pin Arrangement

HM62W1664HJP

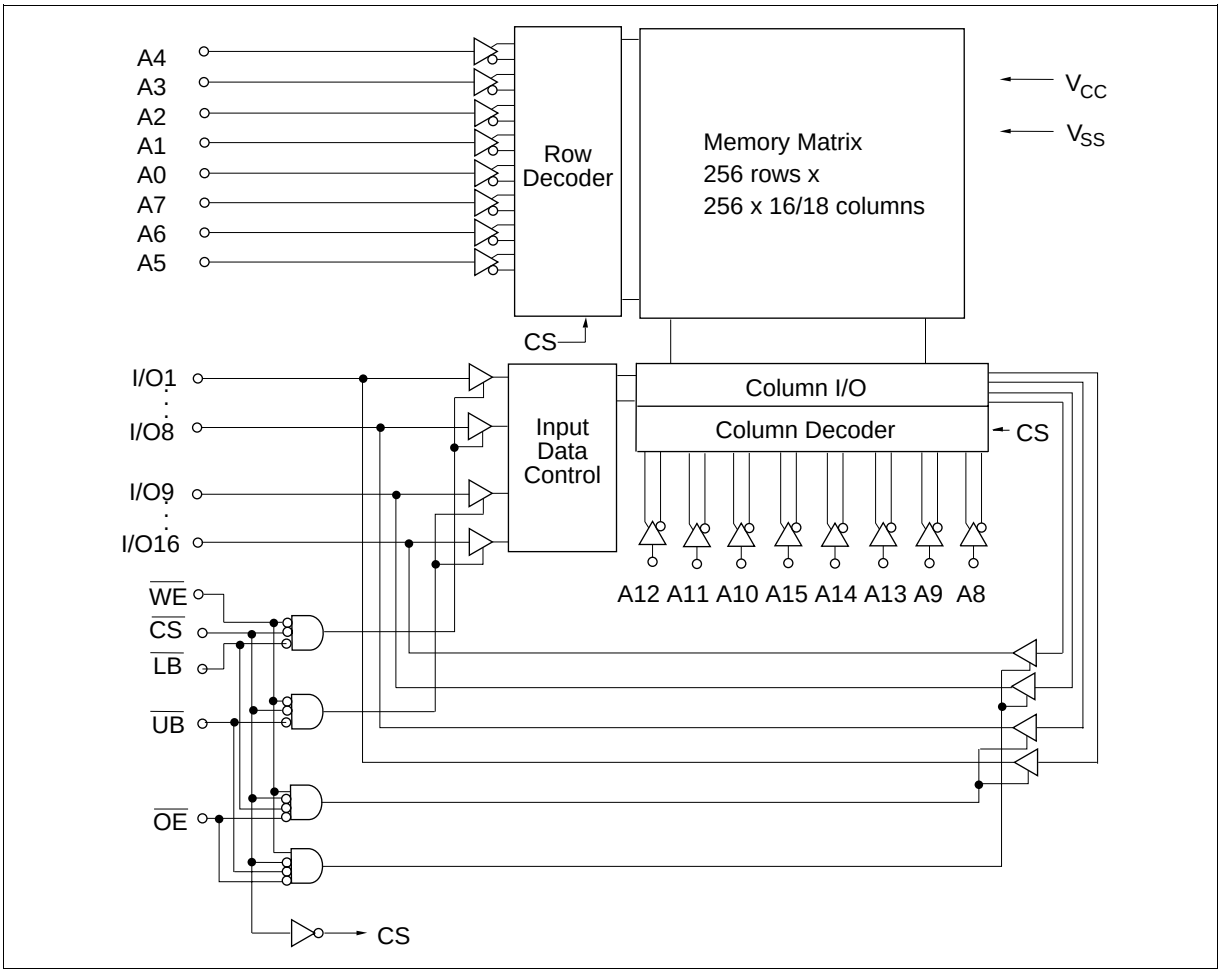


(Top view)

Pin Description

Pin Name	Function
A0 – A15	Address
I/O1 – I/O8	Input/output (lower byte)
I/O9 – I/O16	Input/output (upper byte)
$\overline{CS}$	Chip select
$\overline{LB}$	Lower byte select
$\overline{UB}$	Upper byte select
$\overline{WE}$	Write enable
$\overline{OE}$	Output enable
V_{CC}	Power supply
V_{SS}	Ground
NC	No connection

Block Diagram



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply voltage relative to V_{SS}	V_{CC}	–0.5 to +4.6	V
Voltage on any pin relative to V_{SS}	V_T	–0.5 [*1] to V_{CC} + 0.5	V
Power dissipation	P_T	1.0	W
Operating temperature	Topr	0 to +70	°C
Storage temperature	Tstg	–55 to +125	°C
Storage temperature under bias	Tbias	–10 to +85	°C

Note: 1. –2.5 V for pulse width (under shoot) ≤ 10 ns

Function Table

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	$\overline{LB}$	$\overline{UB}$	V_{CC} Current	I/O(Lower Byte)	I/O(Upper Byte)	Ref. Cycle
H	X	X	X	X	I_{SB}, I_{SB1}	High-Z	High-Z	—
L	H	H	X	X	I_{CC}	High-Z	High-Z	—
L	L	H	L	L	I_{CC}	Output	Output	Read cycle
L	L	H	L	H	I_{CC}	Output	High-Z	Read cycle
L	L	H	H	L	I_{CC}	High-Z	Output	Read cycle
L	L	H	H	H	I_{CC}	High-Z	High-Z	—
L	X	L	L	L	I_{CC}	Input	Input	Write cycle
L	X	L	L	H	I_{CC}	Input	High-Z	Write cycle
L	X	L	H	L	I_{CC}	High-Z	Input	Write cycle
L	X	L	H	H	I_{CC}	High-Z	High-Z	—

Note: X: H or L

Recommended DC Operating Conditions (Ta = 0 to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage[*2]	V_{CC}	3.0	3.3	3.6	V
	V_{SS}	0	0	0	V
Input voltage	V_{IH}	2.0	—	V_{CC} + 0.3	V
	V_{IL}	–0.3 [*1]	—	0.8	V

Notes: 1. –2.0 V for pulse width (under shoot) ≤ 10 ns
2. The supply voltage with all V_{CC} pins must be on the same level.
The supply voltage with all V_{SS} pins must be on the same level.

DC Characteristics (Ta = 0 to +70°C, V_{CC} = 3.3 V ± 0.3 V, V_{SS} = 0 V)

Parameter	Symbol	Min	Typ[*1]	Max	Unit	Test Conditions	Note
Input leakage current	$\|I_{LI}\|$	—	—	2	µA	Vin = V_{SS} to V_{CC}	
Output leakage current	$\|I_{LO}\|$	—	—	2	µA	$V_{I/O}$ = V_{SS} to V_{CC}	
Operating power supply current	I_{CC}	—	80	110	mA	30 ns cycle	$\overline{CS}$ = V_{IL}, Iout = 0 mA Other inputs = V_{IH}/V_{IL}	
		—	70	100	mA	35 ns cycle		
		—	60	90	mA	45 ns cycle		
Standby power supply current	I_{SB}	—	18	35	mA	30 ns cycle	$\overline{CS}$ = V_{IH}, Other inputs = V_{IH}/V_{IL}	
		—	15	30	mA	35 ns cycle		
		—	13	25	mA	45 ns cycle		
Standby power supply current (1)	I_{SB1}	—	—	1	mA	V_{CC} ≥ $\overline{CS}$ ≥ V_{CC} – 0.2 V, 0 V ≤ Vin ≤ 0.2 V or V_{CC} ≥ Vin ≥ V_{CC} – 0.2 V	
		—	—	0.15	mA		L-version
Output voltage	V_{OL1}	—	—	0.2	V	I_{OL1} = 0.1 mA	
	V_{OL2}	—	—	0.4	V	I_{OL2} = 2 mA	
	V_{OH1}	V_{CC} –0.2	—	—	V	I_{OH1} = –0.1 mA	
	V_{OH2}	2.4	—	—	V	I_{OH2} = –2 mA	

Note: 1. Typical values are at V_{CC} = 3.3 V, Ta = +25°C and specified loading.

Capacitance (Ta = 25°C, f = 1.0 MHz)[*1]

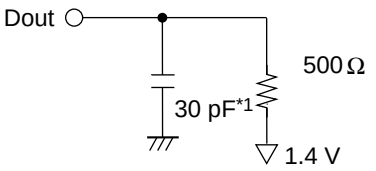
Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
Input capacitance	Cin	—	—	6	pF	Vin = 0 V
Input/output capacitance	$C_{I/O}$	—	—	8	pF	$V_{I/O}$ = 0 V

Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics (Ta = 0 to +70°C, V_{CC} = 3.3 V ± 0.3 V, unless otherwise noted.)

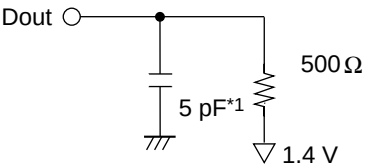
Test Conditions

- Input pulse levels: 2.4 V / 0.4 V
- Input rise and fall time: 3 ns
- Input and output timing reference levels: 1.4 V
- Output load: See figures



Output load (A)

Note: 1. Including scope and jig



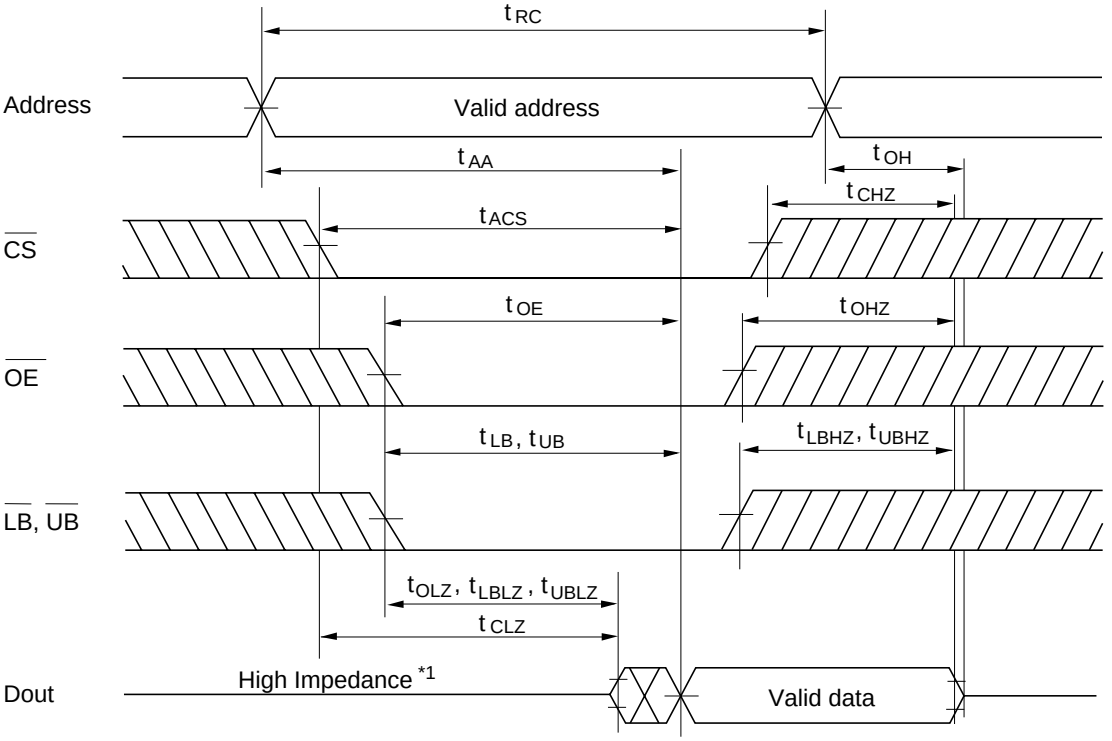
Output load (B)
(for t_{CLZ}, t_{OLZ}, t_{LBLZ}, t_{UBLZ}, t_{CHZ}, t_{OHZ}, t_{LBHZ}, t_{UBHZ}, t_{WHZ}, and t_{OW})

Read Cycle

		HM62W1664H							
		-30		-35		-45			
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit	Note
Read cycle time	t_{RC}	30	—	35	—	45	—	ns	
Address access time	t_{AA}	—	30	—	35	—	45	ns	
Chip select access time	t_{ACS}	—	30	—	35	—	45	ns	
Output enable to output valid	t_{OE}	—	15	—	20	—	25	ns	
Byte select to output valid	t_{LB}, t_{UB}	—	15	—	20	—	25	ns	
Output hold from address change	t_{OH}	5	—	5	—	5	—	ns	
Chip select to output in low-Z	t_{CLZ}	5	—	5	—	5	—	ns	1
Output enable to output in low-Z	t_{OLZ}	1	—	1	—	1	—	ns	1
Byte select to output in low-Z	t_{LBLZ},t_{UBLZ}	1	—	1	—	1	—	ns	1
Chip deselect to output in high-Z	t_{CHZ}	—	12	—	12	—	12	ns	1
Output disable to output in high-Z	t_{OHZ}	—	12	—	12	—	12	ns	1
Byte deselect to output in high-Z	t_{LBHZ}, t_{UBHZ}	—	12	—	12	—	12	ns	1

Note: 1. Transition is measured ±200 mV from steady voltage with Load (B). This parameter is sampled and not 100% tested.

Read Timing Waveform ($\overline{WE}$ = V_{IH})



Note: 1. When $\overline{CS}$, $\overline{OE}$ and $\overline{LB}$ are low, Dout (lower byte) is low impedance.
When $\overline{CS}$, $\overline{OE}$ and $\overline{UB}$ are low, Dout (upper byte) is low impedance.

Write Cycle

		HM62W1664H							
		-30		-35		-45			
Parameter	**Symbol**	**Min**	**Max**	**Min**	**Max**	**Min**	**Max**	**Unit**	**Notes**
Write cycle time	t_{WC}	30	—	35	—	45	—	ns	
Address valid to end of write	t_{AW}	20	—	25	—	30	—	ns	
Chip select to end of write	t_{CW}	20	—	25	—	30	—	ns	
Write pulse width	t_{WP}	20	—	25	—	30	—	ns	
Byte select to end of write	t_{LBW}, t_{UBW}	20	—	25	—	30	—	ns	
Address setup time	t_{AS}	0	—	0	—	0	—	ns	2
Write recovery time	t_{WR}	0	—	0	—	0	—	ns	3
Data to write time overlap	t_{DW}	15	—	20	—	25	—	ns	
Data hold from write time	t_{DH}	0	—	0	—	0	—	ns	
Write disable to output in low-Z	t_{OW}	5	—	5	—	5	—	ns	4
Write enable to output in high-Z	t_{WHZ}	—	12	—	12	—	12	ns	4

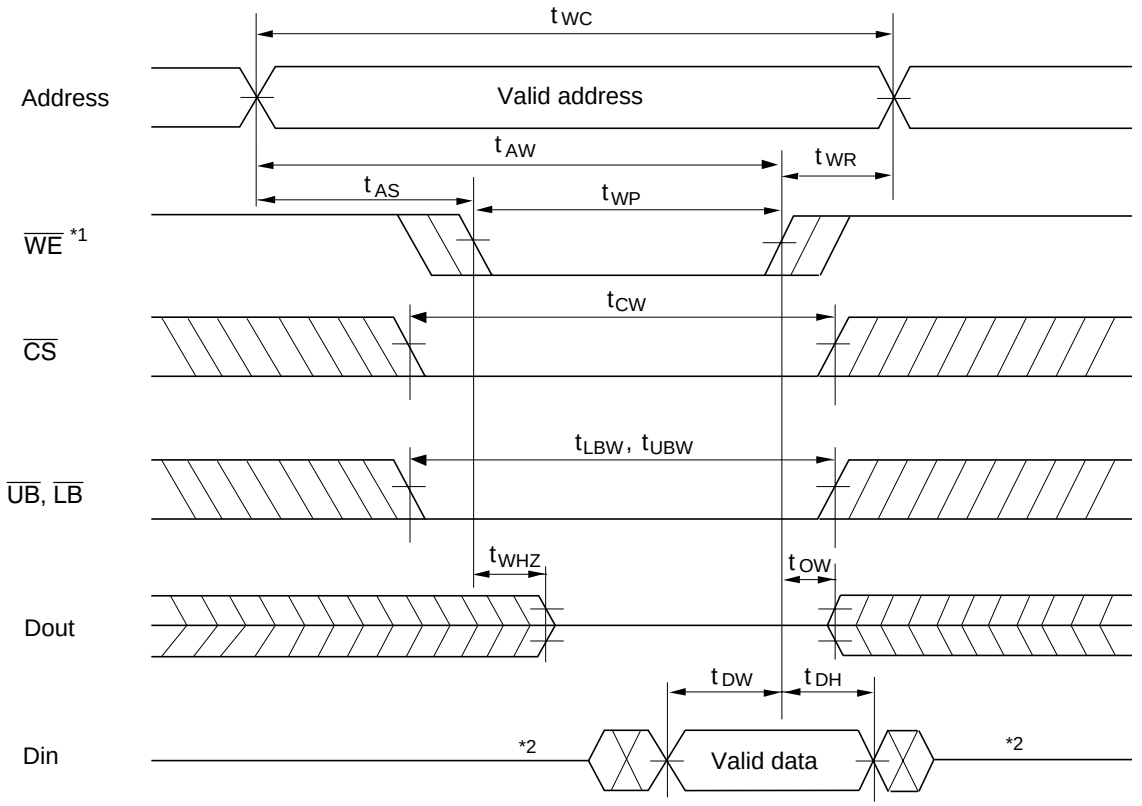
Notes: 1. A write occurs during the overlap of low $\overline{CS}$, low $\overline{WE}$ and low $\overline{LB}$ or low $\overline{UB}$.

2. t_{AS} is measured from the latest address transition to the latest of $\overline{CS}$, $\overline{WE}$, $\overline{LB}$ or $\overline{UB}$ going low.

3. t_{WR} is measured from the earliest of $\overline{CS}$, $\overline{WE}$, $\overline{LB}$ or $\overline{UB}$ going high to the first address transition.

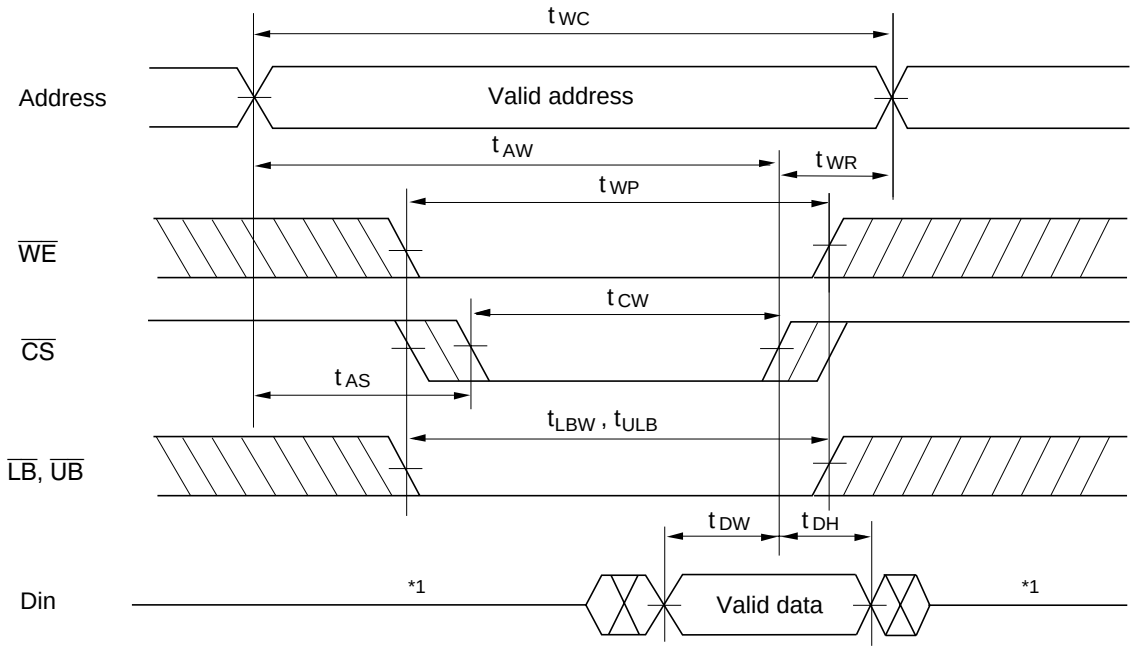
4. Transition is measured ±200 mV from high impedance state's voltage with Load (B). This parameter is sampled and not 100% tested.

Write Timing Waveform (1) ($\overline{WE}$ Controlled)



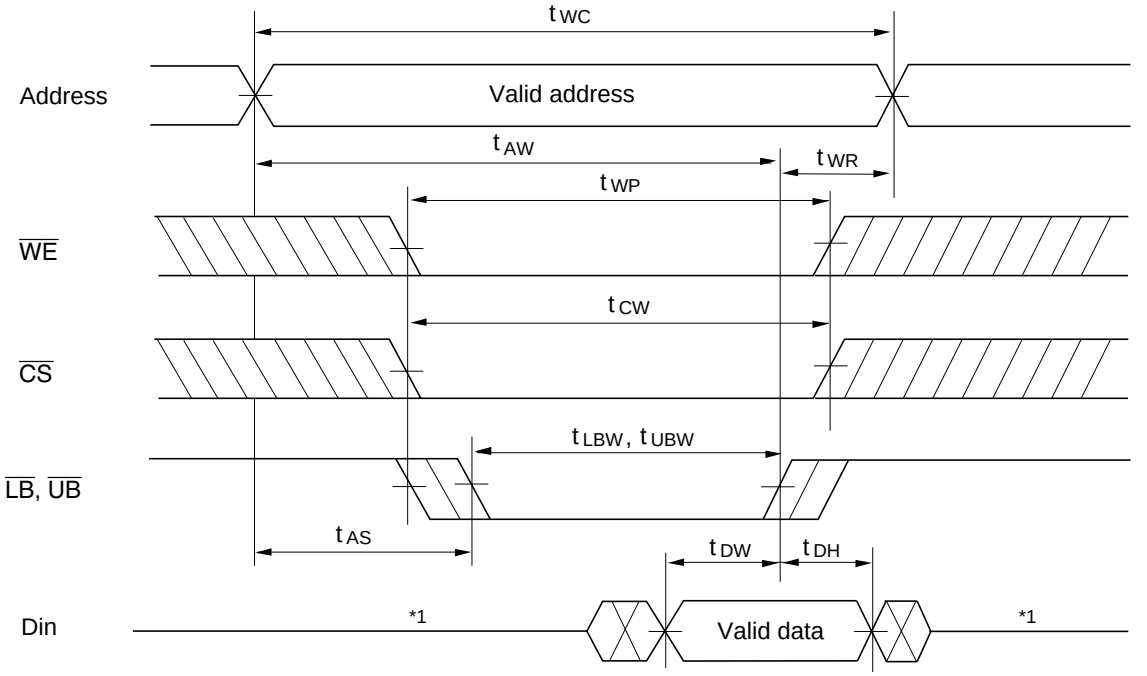
Notes: 1. $\overline{WE}$ must be high during address transition except when the device is disabled with $\overline{CS}$, $\overline{LB}$ or $\overline{UB}$.
2. If $\overline{CS}$, $\overline{OE}$, $\overline{LB}$ and $\overline{UB}$ are low during this period, I/O pins are in the output state. Then, the data input signals of opposite phase to the outputs must not be applied to them.

Write Timing Waveform (2) ($\overline{CS}$ Controlled)



Note: 1. If the $\overline{CS}$ or $\overline{LB}$ or $\overline{UB}$ low transition occurs simultaneously with the $\overline{WE}$ low transition or after the $\overline{WE}$ transition, output remains a high impedance state.

Write Timing Waveform (3) ($\overline{LB}$, $\overline{UB}$ Controlled)



Note: 1. If the $\overline{CS}$ or $\overline{LB}$ or $\overline{UB}$ low transition occurs simultaneously with the $\overline{WE}$ low transition or after the $\overline{WE}$ transition, output remains a high impedance state.

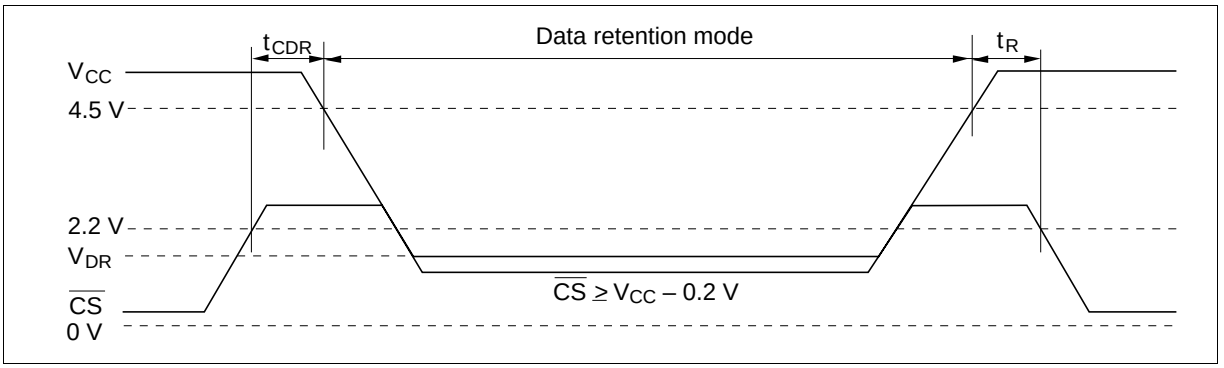
Low V_{CC} Data Retention Characteristics (Ta = 0 to +70°C)

This characteristics is guaranteed only for L-version.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions
V_{CC} for data retention	V_{DR}	2.0	—	—	V	$V_{CC} \geq \overline{CS} \geq V_{CC} - 0.2$ V, $V_{CC} \geq Vin \geq V_{CC} - 0.2$ V or 0 V ≤ Vin ≤ 0.2 V
Data retention current	I_{CCDR}	—	2	80*1	µA	
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	
Operation recovery time	t_R	5	—	—	ms	

Note: 1. V_{CC} = 3.0 V

Low V_{CC} Data Retention Timing Waveform



Package Dimension

HM62W1664HBJP/HBLJP Series (CP-44D) Unit: mm